

# PBSS4021NX,115 Datasheet

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DiGi Electronics Part Number
Manufacturer
Manufacturer Product Number
Description
Detailed Description

PBSS4021NX,115-DG

Nexperia USA Inc.

PBSS4021NX,115

TRANS NPN 20V 7A SOT89

Bipolar (BJT) Transistor NPN 20 V 7 A 115MHz 2.5 W Surface Mount SOT-89

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# Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PBSS4021NX,115	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	7 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
20 V	210mV @ 350mA, 7A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100nA	250 @ 4A, 2V
Power - Max:	Frequency - Transition:
2.5 W	115MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-243AA	SOT-89
Base Product Number:	
PBSS4021	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	



20 V, 7 A NPN low VCEsat transistor

16 January 2025

**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PX

## 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- + High collector current capability  ${\rm I}_{\rm C}$  and  ${\rm I}_{\rm CM}$
- + High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
  - Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

## 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	20	V
I <sub>C</sub>	collector current			-	-	7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	15	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 5 A; $I_B$ = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	15	28	mΩ

## 5. Pinning information

## Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base		B — [x E
			SOT89	sym042

# nexperia

## 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS4021NX	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>			

## 7. Marking

Table 4. Marking codes	
Type number	Marking code[1]
PBSS4021NX	%6D

[1] % = placeholder for manufacturing site code

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	20	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	15	А
I <sub>B</sub>	base current			-	1	А
P <sub>tot</sub> total power dissipation	total power dissipation $T_{amb} \le 25 \degree C$	[1]	-	600	mW	
			[2]	-	1.5	W
			[3]	-	1.45	W
			[4]	-	2.45	W
			[5]	-	2.5	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided,  $35 \ \mu m$  copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

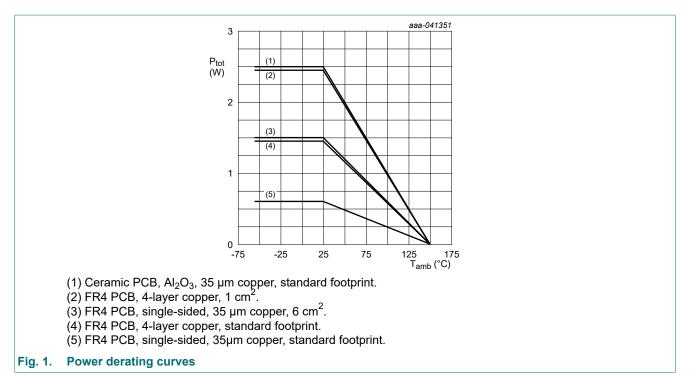
[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 µm copper, tin-plated and standard footprint.

# PBSS4021NX

## 20 V, 7 A NPN low VCEsat transistor



## 9. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from in free air	in free air	[1]	-	-	208	K/W	
	junction to ambient		[2]	-	-	83	K/W
			[3]	-	-	86	K/W
			[4]	-	-	51	K/W
			[5]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

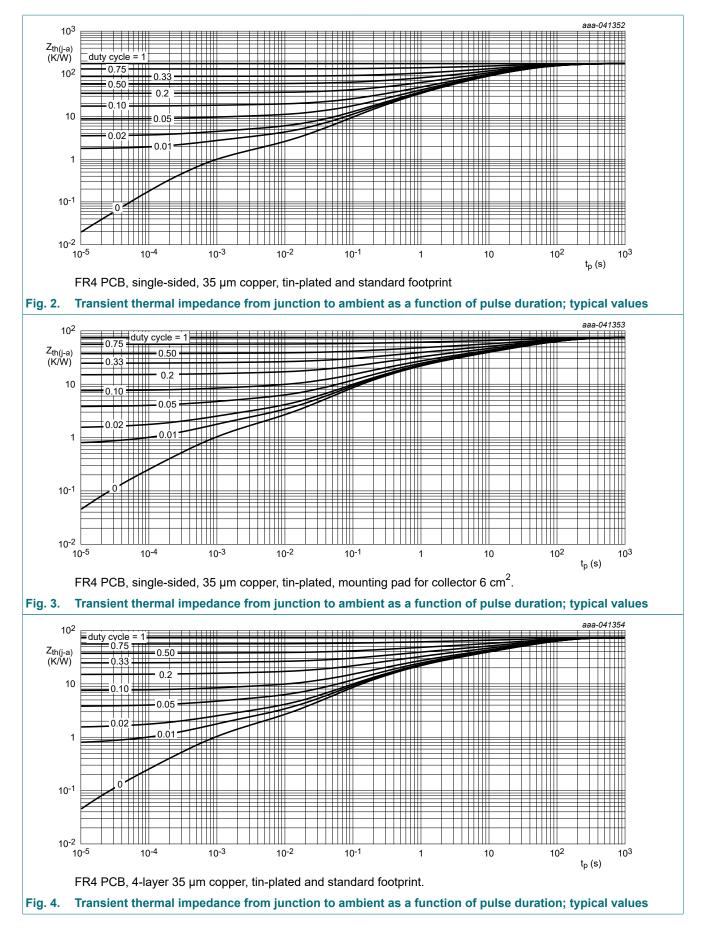
[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>

[5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 µm copper, tin-plated and standard footprint.

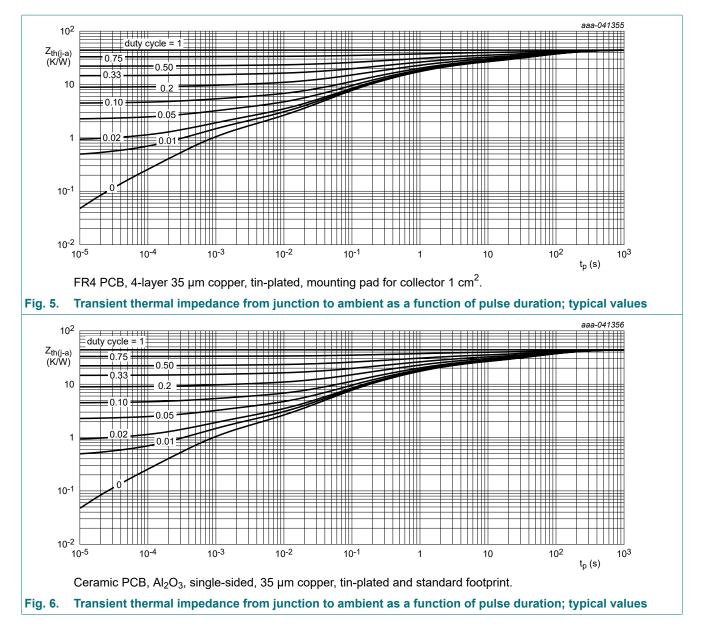
# PBSS4021NX

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20 V, 7 A NPN low VCEsat transistor

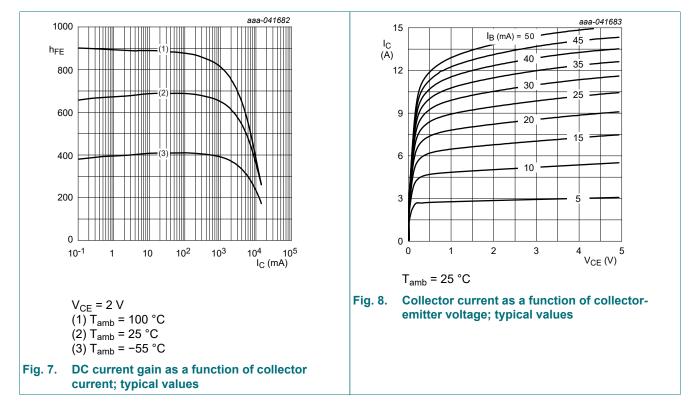
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	20	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	20	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage	$I_E$ = 100 µA; $I_C$ = 0 A; $T_{amb}$ = 25 °C	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 20 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
	current	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 16 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; I <sub>C</sub> = 0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	620	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 1 A; pulsed; } t_{p} \texttt{\leq 300 } \mu s; \\ \delta \texttt{\leq } 0.02;  T_{amb} \texttt{= 25 }^\circ C \end{array} $	300	600	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 2 A; pulsed; } t_{p} \texttt{\leq } 300 \ \mu \texttt{s}; \\ \delta \texttt{\leq } 0.02; \ T_{amb} \texttt{= 25 °C} \end{array} $	300	570	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 4 A; pulsed; } t_{p} \texttt{\le 300 \mu s;} \\ \delta \texttt{\le } 0.02;  T_{amb} \texttt{= 25 °C} \end{array} $	250	510	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 8 A; pulsed; } t_{p} \texttt{\leq 300 } \mu s; \\ \delta \texttt{\leq } 0.02;  T_{amb} \texttt{= 25 }^\circ C \end{array}$	100	400	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 10 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	30	60	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	20	38	mV
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 40 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	40	75	mV
		I <sub>C</sub> = 4 A; I <sub>B</sub> = 40 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	80	140	mV
		$I_{C}$ = 4 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	65	120	mV
		$I_{C}$ = 7 A; $I_{B}$ = 350 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	110	210	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 5 A; I <sub>B</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	15	28	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	0.85	0.9	V
		I <sub>C</sub> = 4 A; I <sub>B</sub> = 400 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	0.99	1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 2 V; I <sub>C</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; T <sub>amb</sub> = 25 °C	-	0.76	0.85	V

# PBSS4021NX

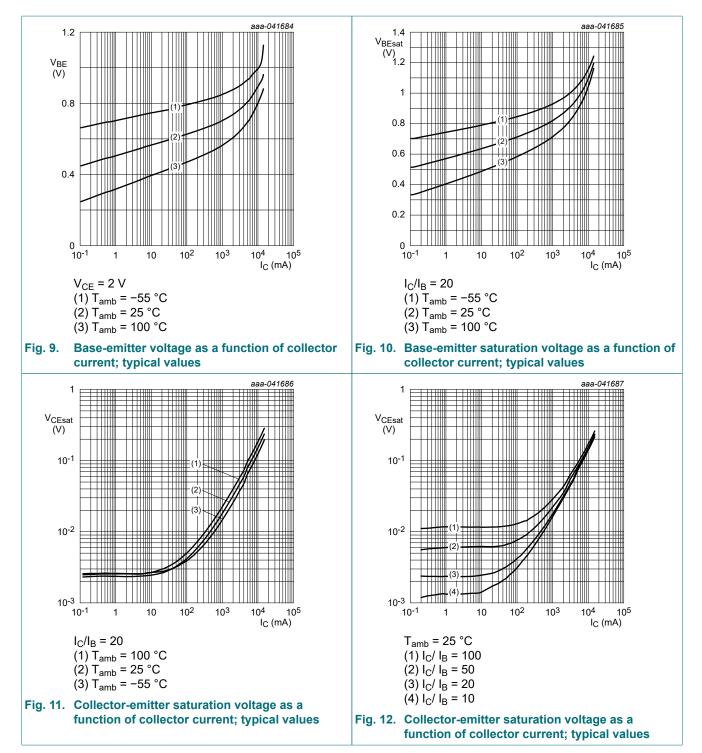
## 20 V, 7 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 50 mA;	-	40	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	35	-	ns
t <sub>on</sub>	turn-on time		-	75	-	ns
t <sub>s</sub>	storage time		-	430	-	ns
t <sub>f</sub>	fall time		-	65	-	ns
t <sub>off</sub>	turn-off time		-	495	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	70	-	pF



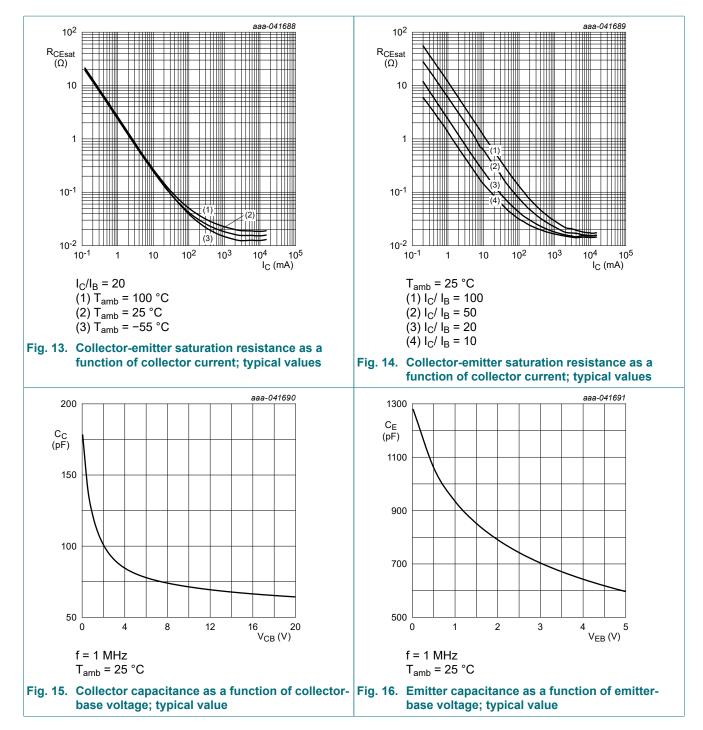
# PBSS4021NX

#### 20 V, 7 A NPN low VCEsat transistor



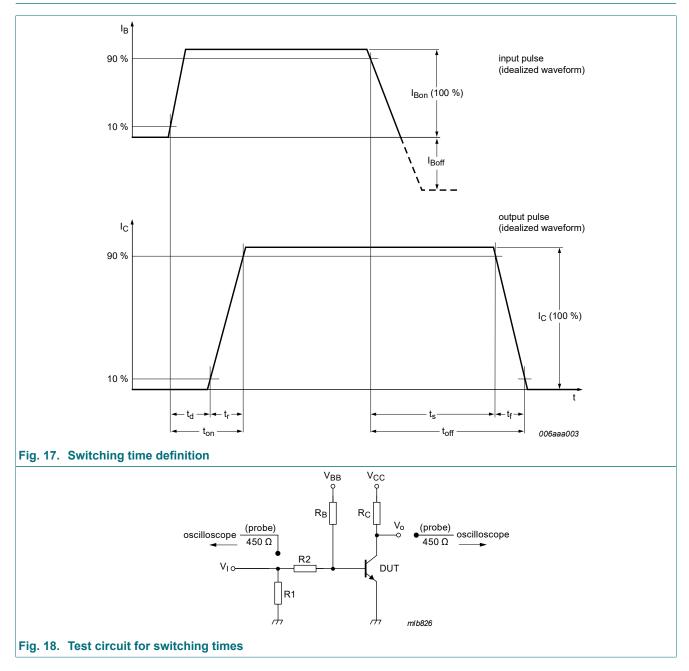
# PBSS4021NX

#### 20 V, 7 A NPN low VCEsat transistor



#### 20 V, 7 A NPN low VCEsat transistor

# **11. Test information**

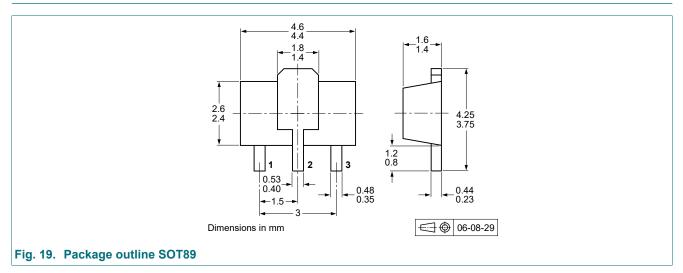


## **Quality information**

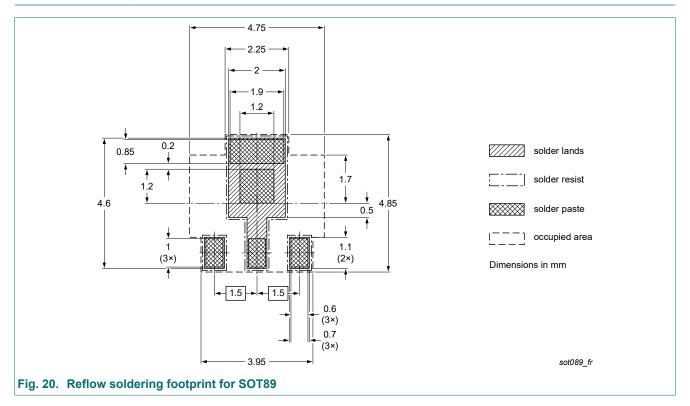
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 20 V, 7 A NPN low VCEsat transistor

# 12. Package outline

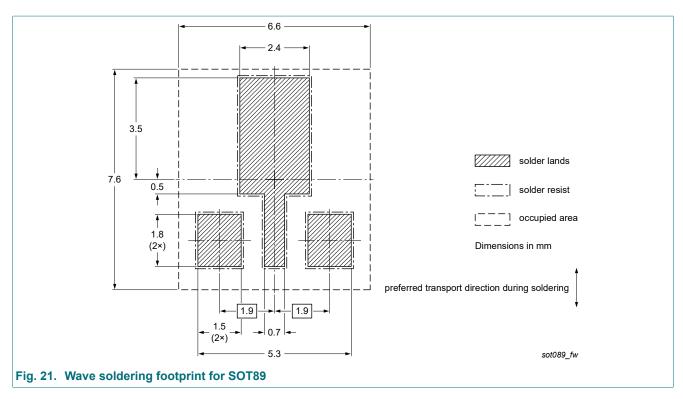


## 13. Soldering



# PBSS4021NX

## 20 V, 7 A NPN low VCEsat transistor



## 20 V, 7 A NPN low VCEsat transistor

# 14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NX v.4	20250116	Product data sheet	-	PBSS4021NX v.3
Modifications:	<ul><li>Editorial updat</li><li>New graphics</li></ul>	te and values are added.		
PBSS4021NX v.3	20121211	Product data sheet	-	PBSS4021NX v.2
	20121009	Product data sheet	-	PBSS4021NX v.1
PBSS4021NX v.2	20121000			

## 20 V, 7 A NPN low VCEsat transistor

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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